

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC4479

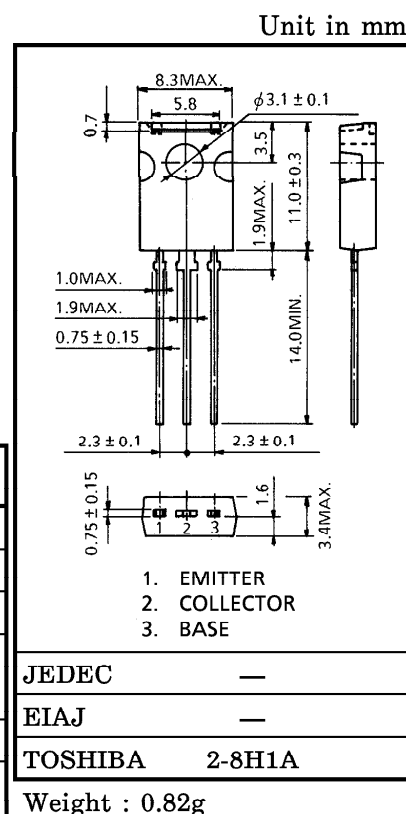
VIDEO OUTPUT APPLICATIONS FOR SUPER HIGH RESOLUTION DISPLAY.

HIGH SPEED SWITCHING APPLICATIONS.

- High Transition Frequency : $f_T = 1.1\text{GHz}$ (Typ.)
- Low Collector Output Capacitance : $C_{ob} = 4.2\text{pF}$ (Typ.)
- High Voltage : $V_{CEO} = 100\text{V}$
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

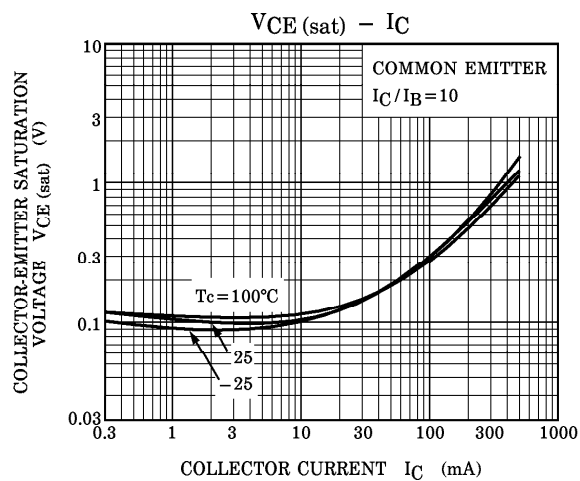
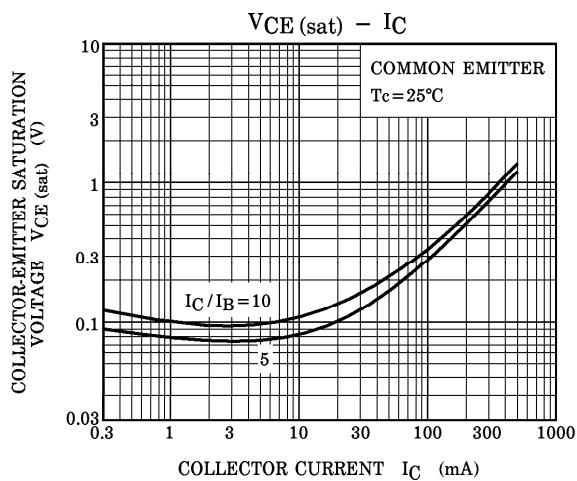
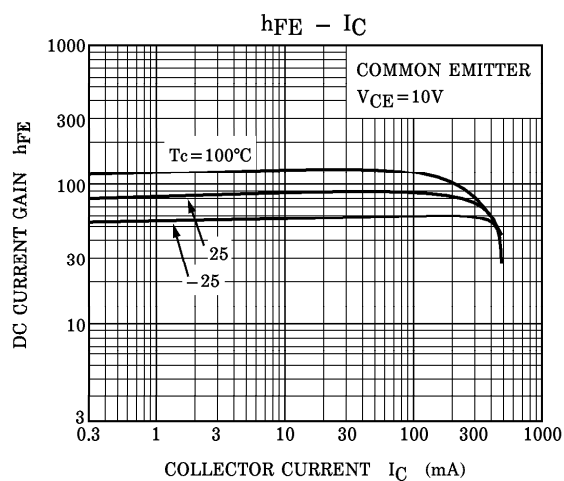
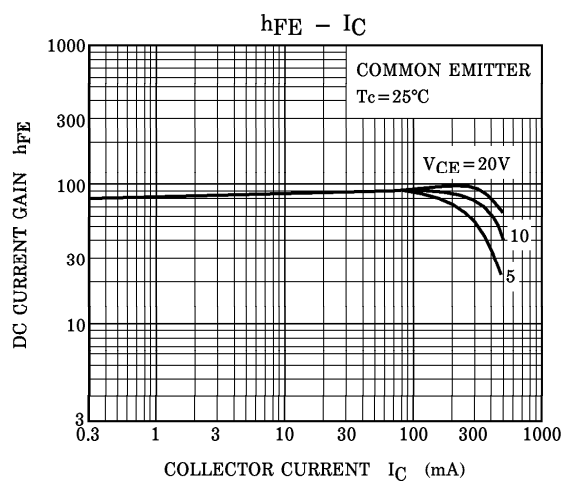
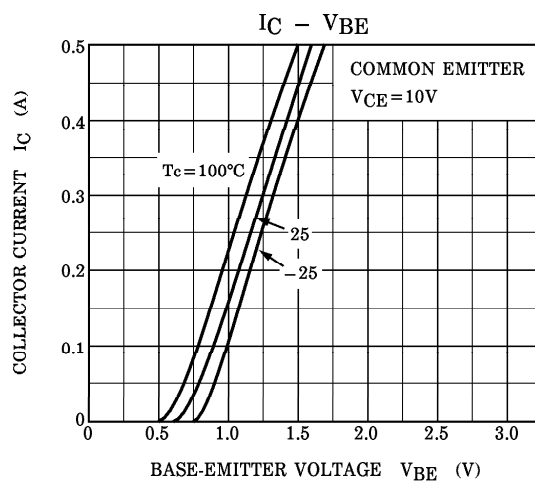
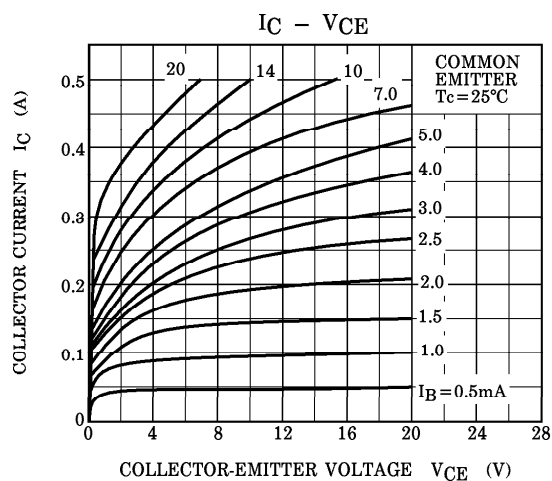
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	3	V
Collector Current	DC	I_C	0.5	A
	Pulse	I_{CP}	1.0	
Base Current		I_B	0.2	A
Collector Power Dissipation	$T_a = 25^\circ\text{C}$	P_C	1.5	W
	$T_c = 25^\circ\text{C}$		10	
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 100\text{V}, I_E = 0$	—	—	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 1\text{mA}, I_B = 0$	100	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$	30	—	240	
	$h_{FE(2)}$	$V_{CE} = 10\text{V}, I_C = 300\text{mA}$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300\text{mA}, I_B = 30\text{mA}$	—	—	3.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 300\text{mA}, I_B = 30\text{mA}$	—	—	2.5	V
Transition Frequency	f_T	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$	800	1100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 30\text{V}, f = 1\text{MHz}, I_E = 0$	—	4.2	5.0	pF

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